

METHODS OF FABRICATING INTEGRATED CIRCUIT DEVICES PROVIDING IMPROVED SHORT PREVENTION

Related Application

This application is a divisional application of co-pending United States Patent Application Serial No. 10/052,721, filed on January 18, 2002, and claims the benefit of Korean Patent Application No. 2001-3066, filed January 19, 2001, the disclosures
5 of which are hereby incorporated herein by reference.

Field of the Invention

The present invention relates to methods of fabricating integrated circuit devices and, more particularly, to methods of fabricating integrated circuit devices
10 having self aligned contacts.

Background of the Invention

As integrated circuit devices decrease in size, the space available for wiring the device and a space between wirings within the device also decrease. For example, in
15 order to form a contact that connects isolated device areas to each other through a highly conductive thin film, an aligning margin and a device isolation margin are typically utilized, thus a relatively large space is conducive to forming the integrated circuit device.

In a memory device, such as a Dynamic Random Access Memory (DRAM), the
20 size of the contact is a factor used to determine the size of the memory cell. Recently, a manufacturing technique has been developed for manufacturing integrated circuit devices having a size of, for example, less than about .25 μm . It is typically difficult to form a fine contact using conventional fabrication methods. Furthermore, in memory devices having a plurality of conductive layers, the spacing between conductive layers is
25 typically increased by the presence of an insulating layer interposed therebetween, thus possibly making it difficult to form the contact between the conductive layers. Therefore, in memory cells having a compact design and repeating patterns, self-aligned contacts are typically used to reduce the cell area.

A self-aligned contact is typically formed using step differences of peripheral structures. Various contacts may be obtained without using a mask by using the height of the peripheral structure, the thickness of an insulation film in a predetermined area where the contact is formed, and an etching method. A possible advantage of the self-aligned contact technique is that a fine contact can be formed without an aligning margin. A conventional self-aligned contact technique typically has a contact hole that is formed using an anisotropic etching process using an etching selectivity between an oxide film and a nitride film.

Now referring to **Figures 1A and 1B**, cross-sectional views of conventional integrated circuits having self-aligned contacts will be discussed below. Referring to **Figure 1A**, a MOS transistor (not shown) is formed on an microelectronic substrate **10** having an active area defined by a field oxide film **12**. A first insulating layer **14** consisting of silicon oxide is formed by depositing silicon oxide on the surface of the microelectronic substrate **10**. A conductive layer for a bit line **BL** and a second insulating layer consisting of silicon nitride are deposited on the first insulating layer **14**. A photolithography process is carried out for patterning the second insulating layer and the conductive layer, so that bit line structures **BL** consisting of a second insulation film pattern **18** and a bit line **16** are formed. Silicon nitride is deposited on the surface of the resulting structure thereby forming a silicon nitride layer. The silicon nitride layer is anisotropically etched so as to form a spacer **20** consisting of silicon nitride on the sidewalls of the bit line structure **BL**.

Now referring to **Figure 1B**, a third insulating layer **22** consisting of silicon oxide is formed by depositing silicon oxide on the surface of the resulting structure. A photoresist pattern (not shown) is formed in such a manner that a contact hole larger than the space between the bit line structures **BL** can be defined. The third insulating layer **22** is etched by an anisotropic etching process using the etching selectivity between a silicon oxide film and a silicon nitride film, thereby forming a storage node contact hole **24** for exposing a substrate area between the bit line structures **BL**. The photoresist pattern is used as an etching mask. A capacitor electrode (not shown) may be provided to bury the node contact hole **24**.

The silicon nitride film may be used as the spacer **20**, which is formed at the sidewall of the bit line structure **BL**, and the silicon oxide film may be used as the third insulating layer **22**. However, since the bond energy of the silicon oxide film may be

greater than the bond energy of the silicon nitride film, it may be difficult to increase the etching selectivity between the silicon oxide film and the silicon nitride film as the size of the storage node contact hole **24** decreases.

Typically, a predetermined space is provided between the bit line structures **BL**,
5 *i.e.* storage node contact hole **24**, by using the self-aligned contact process. If the width of the sidewall spacer **20** is reduced to increase the spacing, the sidewall spacer **20** may be consumed during the etching process for forming the self-aligned contact. Thus, a short may occur. Alternatively, if the width of the sidewall spacer **20** is increased, it may be difficult to bury a gap formed between the bit line structures **BL** as discussed above.

10 In addition, the sidewall spacer **20**, consisting of silicon nitride, typically has a dielectric constant above 7. Thus, the parasitic capacitance between the bit lines may be twice the parasitic capacitance of the conventional contact structure in which the bit line is insulated from the storage electrode by using the silicon oxide film having the dielectric constant of 3.9.

15 Recently, to address the short comings of existing conventional structures, a method for forming the sidewall spacer in the contact hole after forming the self-aligned contact while preventing a short between the storage electrode and the bit line has been discussed. For example, this method is discussed in Japanese Patent No. JP9097880A2 entitled *Semiconductor Storage Device and Its Manufacture* to Hirosuke *et al.*

20 Now referring to **Figures 2A** and **2B**, cross-sectional views of integrated circuits illustrating the method for manufacturing a DRAM cell disclosed in the above referenced Japanese Patent will be discussed. A field oxide film **52** is formed on a microelectronic substrate **50** by using a shallow trench isolation (STI) technique. A conventional MOS transistor manufacturing process is carried out so as to form a MOS
25 transistor consisting of a gate region and a source/drain region on the surface of the substrate **50**.

Silicon oxide is deposited on the surface of the microelectronic substrate **50** forming a silicon oxide film **54**. A contact hole for exposing the source/drain region is formed by using a self-aligned contact process. A pad electrode **56** for burying the
30 contact hole is formed at the same height as the gate. Silicon oxide is deposited on the surface of the resulting structure, thereby forming a first insulating layer **58**.

A conductive layer for a bit line, a second insulating layer consisting of silicon oxide, and a third insulating layer consisting of silicon nitride are sequentially formed on

Referring now to **Figure 2C**, the fourth insulating layer **66** is etched using the high etching selectivity between the silicon oxide film and the silicon nitride film. The first insulating layer **58** formed on the pad electrode **56** is simultaneously etched so that a first insulating layer pattern **58a** is formed. At the same time, a storage node contact hole **68**, which is self-aligned with respect to the bit line structure **BL**, is formed.

The conventional method discussed with respect to **Figures 2A through 2D** may address some of the problems discussed with respect to the methods and devices of Figure 1A through 1B. For example, the gap burying problem caused by the spacer **70** may be improved by forming spacer **70** after forming the storage node contact hole **68** and the increase in the parasitic capacitance between the bit lines **60** may be improved by fabricating the spacer **70** using a silicon oxide film having a low dielectric constant. However, if the bit line structure **BL** has an inclined profile, the height of the spacer **70** may be lowered, thus, a part of the bit line **60**, *i.e.* an upper end portion of the bit line **60** may be exposed, thus, a short may occur between the bit line **60** and the storage electrode.

Embodiments of the present invention provide methods of fabricating integrated circuit devices including a conductive layer disposed on a microelectronic substrate and an insulating layer disposed on the conductive layer. The insulating

layer includes an overhanging portion that extends beyond the conductive layer. A sidewall insulating region is provided laterally adjacent a sidewall of the conductive layer and extends between the overhanging portion of the insulating layer and the microelectronic substrate.

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Some embodiments of the present invention may include an insulating region disposed between the overhanging portion of the insulating layer and the microelectronic substrate. A sidewall spacer may be formed that conforms to a sidewall of the insulating layer, the sidewall insulating region and an adjoining surface of the insulating region.

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In further embodiments of the present invention, the conductive layer may be formed by adjusting the etchant so that the insulating layer includes the overhanging portion that extends beyond the conductive layer. The conductive layer may further include first and second metallic layers.

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Brief Description of the Drawings

Figures 1A and 1B are cross-sectional views of a portion of a substrate of a conventional integrated circuit devices having a self-aligned contact;

Figures 2A through 2D are cross-sectional views of a portion of a substrate of another conventional integrated circuit device having a self-aligned contact;

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Figures 3A to 3E are cross-sectional views of a portion of an integrated circuit device according to embodiments of the present invention illustrating methods fabricating the same;

Figure 4 is a plan view of a Dynamic Random Access Memory (DRAM) cell according to the embodiments of the present invention;

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Figure 5 is a cross-sectional view of the DRAM cell in of **Figure 4** taken along the line B-B'; and

Figures 6A through 13B are cross-sectional views of a DRAM cell according to embodiments of the present invention illustrating methods of fabrication the same.

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Detailed Description of the Invention

The present invention now will be described more fully with reference to the accompanying drawings, in which preferred embodiments of the invention are shown.

This invention may, however, be embodied in many different forms and should not be construed as being limited to the embodiments set forth herein; rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the concept of the invention to those skilled in the art. In the
5 drawings, the thickness of layers and regions are exaggerated for clarity. It will also be understood that when a layer is referred to as being "on" another layer or substrate, it can be directly on the other layer or substrate, or intervening layers may also be present. In contrast, when an element is referred to as being "directly on" another element, there are no intervening elements present. Like reference numerals refer to
10 like elements throughout.

Embodiments of the present invention will now be described in detail below with reference to **Figures 3A through 13B**, which illustrate various embodiments of the present invention and various processes of fabricating embodiments of the present invention. An integrated circuit device is provided having an insulating layer that
15 includes an overhanging portion that extends beyond the conductive layer. A sidewall insulating region, *i.e.* insulating layer residue, is disposed laterally in the space between the overhanging portion of the insulating layer and the microelectronic substrate. Accordingly, this sidewall insulating region may reduce the possibility that the conductive layer will be exposed and cause a short when the contact hole is etched

20 Now referring to **Figures 3A through 3E**, cross-sectional views of integrated circuits according to embodiments of the present invention illustrating fabrication methods of the same will be discussed. A first insulating layer **102** is formed on an microelectronic substrate **100**, a conductive layer **107** is formed on the first insulating layer **102**, and a second insulating layer **108** is formed on the conductive layer **107**. The
25 first insulating layer **102** may be formed by, for example, depositing silicon oxide based materials on the microelectronic substrate **100**. The conductive layer **107** may include, for example, a first layer **104** and a second layer **106**. The first layer **104** may include, for example, a first metal and a compound of the first metal, such as titanium/titanium nitride (Ti/TiN). The second layer **106**, may include, a second metal, such as tungsten
30 (W). The second insulating layer **108** may be formed, for example, using a silicon nitride based material. Alternatively, the second insulating layer **108** may be a composite layer having a silicon nitride based material and a silicon oxide based material.

Before forming the conductive layer **107**, the first insulating layer **102** may be

partially etched via a photolithography process so that a first contact hole (not shown) may be formed for exposing a first lower area of the first insulating layer **102**. Thus, the conductive layer **107** is electrically connected to the first lower area of the first insulating layer **102** through the first contact hole.

5 A contact plug (not shown) having a barrier metal layer and a third metal layer may be formed in the first contact hole, after forming the first contact hole and before forming the conductive layer **107**. The contact plug may be formed by depositing the barrier metal layer on the first contact hole and on the first insulating layer **102**, depositing the third metal on the barrier metal layer and removing the third metal formed
10 on the first insulating layer **102**. The barrier metal layer may include, for example, titanium/titanium nitride (Ti/TiN), and the third metal layer may include, for example, tungsten (W). Optionally, a contact plug may be provided. If a contact plug is provided, the conductive layer **107** may be fabricated in a single layer using a fourth metal, such as tungsten.

15 Referring now to **Figure 3B**, the second insulating layer **108** and the conductive layer **107** are patterned to form a wiring **L**. A photoresist is coated on the second insulating layer **108** by, for example, using a spin coating method thereby forming a photoresist film. The photoresist film is subject to a photo process so as to form a first photoresist pattern (not shown). The second insulating layer **108** and the conductive
20 layer **107** are etched to form the wiring **L** having a second insulating layer pattern **108a** and a conductive layer pattern **107a**. The first photoresist pattern may be used as an etching mask. The conductive layer pattern **107a** is provided having a width that is smaller than a width of the second insulating layer pattern **108a**. The width of the conductive layer pattern may be controlled by adjusting an etchant recipe of the
25 conductive layer **107**. The conductive layer **107** may include a first layer **104** and a second layer **106**. As discussed above, the first layer **104** may include titanium/titanium nitride (Ti/TiN) and the second layer **106** may include tungsten.

 The second insulating layer pattern **108a** is formed by etching the second insulating layer **108** using an anisotropic etching process. Undercut portions are formed
30 at one or both lower sides of the second insulating layer pattern **108a**, for example, by adjusting the etchant recipe of the second layer **106**. Thus, as illustrated, the second layer pattern **106a** has a width that is narrower than the width of the second insulation pattern **108a** by from about 10 to about 100 Å (**d**). Similarly, the etching recipe of the first layer

104 is controlled so as to form a first layer pattern **104a** having a width which is narrower than the width of the second insulating layer pattern **108a** by from about 10 to 100 Å (**d**). Thus, the second insulating layer **108a** includes an overhanging portion that extends beyond the conductive layer by from about 10 to about 100 Å (**d**).

5 It will be understood that although the widths of the second layer pattern **106a** and the first layer pattern **104a** are both discussed as being narrower than the second insulating layer pattern by the width **d**, the present invention is not limited to this configuration. For example, the width of the first layer pattern **104a** may be substantially the same as the width of the second layer pattern **106a**. Alternatively, the width of the
10 first layer pattern **104a** may be substantially different than the width of the second layer pattern **106a**. Furthermore, the undercut portion may be formed on one side of the second insulating layer pattern **108a** or on both sides of the second insulating layer pattern **108a** as illustrated in **Figure 3B**. If the undercut portion is formed on both sides of the second insulating layer pattern **108a**, the width of the second layer pattern **106a**
15 and the width of the first layer pattern **104a** are smaller than the width of the second insulating layer pattern **108a** by **2d**.

 Referring now to **Figure 3C**, a third insulating layer **110** is formed on the second insulating layer pattern **108a**. The first photoresist pattern is removed by, for example, performing ashing and stripping processes. Silicon oxide based materials are deposited
20 on the surface of the resulting structure with wirings **L** formed thereon, thereby forming a third insulating layer **110**. In some embodiments of the present invention, the conductive layer **107** includes tungsten. The third insulating layer **110** may be formed by a high temperature oxide film which is deposited at the high temperature or an oxide film such as Borophosphosilica glass (BPSG) and spin on glass (SOG) which are required to
25 perform a high temperature baking process after the deposition process. In this case, tungsten may be oxidized because the side portion of the conductive layer pattern **107a** may be exposed. Accordingly, in order to prevent the tungsten from oxidizing, a deposition process is carried out in a high density plasma (HDP) process, during which material is deposited in a low temperature and a gap is buried without creating voids,
30 thereby forming the third insulating layer **110** consisting of oxide based material.

 Referring now to **Figure 3D**, a contact hole **114** for forming a storage node is formed. A chemical and mechanical polishing process is carried out so as to planarize the surface of the third insulating layer **110**. A photoresist is coated on the planarized

surface of the third insulating layer **110** thereby forming a photoresist film. A second photoresist pattern **112** for defining a contact hole area is formed by means of a photo process which exposes and develops the photoresist film. The third insulating layer **110** and the first insulating layer **102** are etched using the anisotropic etching process under the etching condition having the high selectivity with respect to the second insulating layer pattern **108a**. The second photoresist pattern **112** may be used as an etching mask. The contact hole **114**, which is self-aligned with respect to the wirings **L**, is formed, and a third insulating layer residue **110a**, *i.e.* a sidewall insulating region, having a thickness (**d**) corresponding to a width difference between the second insulating layer pattern **108a** and the conductive layer pattern **107a** remains on a sidewall of the conductive layer pattern **107a** in the contact hole **114**. The third insulating layer residue **110a** may reduce the possibility that the sidewall of the conductive layer pattern **107a** will be exposed and reduce the current leakage generated in the conductive layer pattern **107a**.

Referring now to **Figure 3E**, after removing the second photoresist pattern **112** through ashing and stripping processes, a fourth insulating layer having a thickness of from about 200 to about 700 Å is deposited on the surface of the resulting structure. The fourth insulating layer is formed, for example, by a method disclosed in an article by J.W. Klaus *et al* entitled *Atomic layer deposition of SiO₂ using catalyzed and uncatalyzed self-limiting surface reaction*. Surface Review and Letters, Volume 6, Nos. 3 & 4, pages 435-448 (1999). The fourth insulating layer is anisotropically etched so that a sidewall spacer **116** is formed in the contact hole **114** from the fourth insulating layer. The sidewall spacer **116** may include, for example, silicon oxide based material or silicon nitride based material. Alternatively, the sidewall spacer **116** may include a composite layer consisting of silicon oxide based material and silicon nitride based material.

Accordingly, the presence of the third insulating layer residue may reduce the possibility that the conductive layer pattern may be exposed when the contact is etched. In addition, the sidewall spacer formed at the sidewall of the wiring typically is thicker than conventional sidewall spacers due to the third insulating layer, thus, reducing the current leakage.

Referring now to **Figures 4 and 5**, a plan view of a dynamic Random Access Memory (DRAM) cell of **Figure 4** and a cross-sectional view of the DRAM cell taken along the line B-B' of **Figure 4** in **Figure 5** will be discussed. MOS transistors consisting of a gate electrode **303**, which is provided as a word line, a capacitor contact

area **305a**, *i.e.* a source region, and a bit line contact area **305b**, *i.e.* a drain region, are provided on an microelectronic substrate **200** in which an active area **201** is defined by a field oxide film **202**. First and second pad electrodes **204a** and **204b** can be formed on source/drain regions **305a** and **305b** of the MOS transistors for reducing the aspect ratio of contact holes formed on the source/drain regions **305a** and **305b**.

A first bit line structure **BL1** and a second bit line structure **BL2** are formed on the microelectronic substrate **200** including MOS transistors. The first and second bit line structures **BL1** and **BL2** are typically spaced apart by a predetermined distance and a storage node contact hole **218** is defined therebetween. The storage node contact hole **218** may expose a capacitor contact area, *i.e.*, the source region **305a** and/or the first pad electrode **204a** making contact with the source region **305a**.

As illustrated, the first bit line structure **BL1** includes a first pattern **205a** of the first insulating layer, a first bit line **208a** formed on the first pattern **205a** of the first insulating layer, and a first pattern **210a** of the second insulating layer. The first pattern **210a** of the second insulating layer is formed on the first bit line **208a** and typically has a width larger than a width of the first bit line **208a**.

Similarly, the second bit line structure **BL2** includes a second pattern **205b** of the first insulating layer, a second bit line **208b** formed on the third pattern **205b** of the first insulating layer, and a second pattern **210b** of the second insulating layer. The second pattern **210b** of the second insulating layer is formed on the second bit line **208b** and typically has a width larger than a width of the second bit line **208b**.

A first residue **216a**, *i.e.* a sidewall insulating region, of the third insulating layer is provided on a sidewall of the first bit line **208a** in the storage node contact hole **218**. The first residue **216a** of the third insulating may have a thickness (**d**) corresponding to a width difference between the first pattern **210a** of the second insulating layer and the first bit line **208a** when measured from a center of the first bit line **208a**. In other words, the width of the first pattern **210a** of the second insulating layer is substantially similar to the sum of the widths of the first bit line **208a** and the first residue **216a** of the third insulating layer, thus, the sidewall of the first pattern **210a** of the second insulating layer can be continuously formed with respect to an outer wall of the first residue **216a** of the third insulating layer.

Similarly, a second residue **216b**, *i.e.* a sidewall insulating region, of the third insulating layer on a sidewall of the second bit line **208b** in the storage node contact hole

218. The second residue **216b** may have a thickness (**d**) corresponding to the width difference between the second pattern **210b** of the second insulating layer and the second bit line **208a**. Thus, the width of the second pattern **210b** of the second insulating layer is substantially similar to the sum of the widths of the second bit line **208b** and the second residue **216b** of the third insulating layer formed at both sides of the second bit line **208b**, thus, the sidewall of the second pattern **210b** of the second insulating layer can be continuously formed with respect to an outer wall of the second residue **216b** of the third insulating layer.

A first sidewall spacer **220a** is formed on the sidewall of the first residue **216a** of the third insulating layer and on the sidewall of the first pattern **205a** of the first insulating layer. A second sidewall spacer **220b** is formed on the sidewall of the second residue **216b** of the third insulating layer and on the sidewall of the third pattern **205b** of the first insulating layer.

A capacitor conductive layer **222** may be formed in the storage node contact hole 218. The capacitor conductive layer **222** is typically self-aligned with respect to the bit line structures **BL1** and **BL2**. As illustrated in the figures, the capacitor conductive layer **222** may be provided in the form of a contact plug. Alternatively, the capacitor conductive plug **222** may be patterned with a storage electrode pattern by means of a photolithography process.

Embodiments of the present invention will now be discussed with reference to **Figures 6A** through **13B**, which illustrate various cross-sectional views of DRAM cells according to embodiments of the present invention. **Figures 6A** through **13A** are cross-sectional views taken along the line A-A' in **Figure 4**. **Figures 6B** through **13B** are cross-sectional views taken along the line B-B' in **Figure 4**.

As illustrated in **Figures 6A** and **6B**, methods of forming first and second pad electrodes **204a** and **204b** will be discussed. The active area (**201** of **Figure 4**) is defined in the substrate **200** by forming the field oxide film **202** on the surface of the substrate **200** through an isolation process, for example, a shallow trench isolation process.

The MOS transistors are formed in the active area **201** of the substrate **200**. After growing a thin gate oxide film **302** on the surface of the active area **201** through a thermal oxidation process, a gate electrode **303** of the MOS transistor, which may act as a word line, is formed on the gate oxide film **302**. The gate electrode **303** typically has a stacked polycide structure. The polycide structure may include a polysilicon layer and a

tungsten polysilicide layer. High density impurities in the polycide structure are doped using a doping process, such as, for example, a diffusing process, an ion implanting process and/or an in-situ doping process. Furthermore, a silicon nitride film **304** is formed on the gate electrode **303** and a sidewall spacer consisting of silicon nitride is formed on the sidewall of the gate electrode **303**. Impurities are implanted into the substrate **200** using the gate electrode **303** as a mask, forming the source/drain regions **305a** and **305b** of the MOS transistor on the surface of the active area **201**.

It will be understood that one of the doping areas is a capacitor contact area making contact with the storage electrode of the capacitor and the other of the doping areas is a bit line contact area making contact with the bit line. For example, the source region **305a** may be the capacitor contact area and the drain region **305b** may be a bit line contact area.

An insulating layer **303** consisting of, for example, oxide material, such as Borophosphosilica glass (BPSG), is deposited on the surface of the substrate **200**. The insulating interlayer **203** is planarized using a chemical-mechanical polishing (CMP) process. The silicon nitride film **304** may be used as a stopper. A contact hole is formed by etching the insulating interlayer **203** using a high etching selectivity between the insulating interlayer **203** and the silicon nitride film **304**. The contact hole may be self-aligned with respect to the gate electrode **303**.

A polysilicon layer, which is typically highly-doped with impurities, is deposited in the contact hole. The polysilicon layer may be removed to expose the silicon nitride film **304**. Accordingly, a first pad electrode **204a** and a second pad electrode **204b** are formed in the contact hole. As illustrated, the first pad electrode **204a** contacts the source region **305a** and the second pad electrode **204b** contacts the drain region **305b**.

As illustrated in **Figures 7A and 7B**, the first insulating layer **205** is formed on the substrates **200** including the first and second pad electrodes **204a** and **204b**. The conductive layer **208** for the bit line is formed on the first insulating layer **205** and the second insulating layer **210** is formed on the conductive layer **208**. **Figure 8A** illustrates a cross-sectional view taken along the line C-C' of **Figure 4**. Referring now to **Figures 7A, 7B and 8A**, the first insulating layer **205** may include, for example, silicon oxide based materials. The first insulating layer **205** is partially etched using, for example, a photolithography process to form a bit line contact hole **211** that may partially or substantially expose the second pad electrode **204b**.

A conductive layer **208** for the bit line is deposited on the bit line contact hole **211** and the first insulating layer **205**. The bit line conductive layer **208** typically has a first layer **206** and a second layer **207**. The first layer **206** may include, for example, a first metal and/or compounds of the first metal, such as Ti/TiN. The second layer **207** may include, for example, a second metal such as tungsten. A second insulating layer **210** is deposited on the conductive layer **208** for the bit line. The second insulating layer **210** may include a silicon nitride based material. Alternatively, the second insulating layer may include a composite layer consisting of silicon oxide based material and silicon nitride based material. The second insulating layer **210** may protect the bit line during the etching process used to form the self-aligned contact.

Accordingly, the bit line conductive layer **208**, which typically has first and second layers, may be formed in direct contact with the bit line contact hole **211**. Alternatively, a bit line plug can be provided in the bit line contact hole **211** and the bit line conductive layer **208** may be formed in direct contact with the bit line plug. Methods of forming the will be discussed further below with reference to **Figure 8B**.

Referring now to **Figure 8B**, which is a cross-sectional view taken along the line C-C' in **Figure 4**. A barrier metal layer **209** is deposited on the bit line contact hole **211** and the first insulating layer **205**. The barrier metal layer may be, for example, a Ti/TiN layer. A third metal layer **212** is deposited on the barrier metal layer **209**. The third metal layer **212** may include, for example, tungsten. The third metal layer **212** is etched to partially or substantially expose the surface of the first insulating layer **205**. A CMP process may also be used. Accordingly, a bit line plug **215** including the barrier metal layer **209** and the third metal layer **212** is formed in the bit line contact hole **211**. The conductive layer **208** for the bit line including a fourth metal, such as tungsten, is deposited on the bit line plug **215** and on the first insulating layer **205**. Accordingly, in some embodiments of the present invention, the bit line conductive layer **208** is fabricated as a single layer.

Referring now to **Figures 9A** and **9B**, methods of fabricating the bit line structures **BL1** and **BL2** will be discussed. The second insulating layer **210** and the conductive layer **208** are etched using a first photoresist pattern (not shown) as an etching mask. Accordingly, a first bit line structure **BL1** and a second bit line structure **BL2** are provided. The first bit line structure **BL1** has the first pattern **210a** of the second insulating layer **210** and the first bit line **208a** and the second bit line structure **BL2** has

the second pattern **210b** of the second insulating layer **210** and the second bit line **208b**. The first and second bit line structures **BL1** and **BL2** are spaced apart by a predetermined distance. The widths of the first and second bit line structures **BL1** and **BL2** are typically smaller than the widths of the first and second patterns **210a** and **210b** of the second
5 insulating layer **210**, respectively.

An anti-reflection layer (not shown) may be formed on the second insulating layer **210** to aid in the photolithography process. The anti-reflection layer is typically a single layer made of, for example, silicon oxynitride (SiON). Alternatively, the anti-reflection layer may include a composite layer of a high temperature oxide film and
10 SiON film. The anti-reflection layer may reduce light from reflecting from the lower substrate when the following photolithography process is carried out.

Referring now to **Figures 10A and 10B**, methods of forming an insulating layer **216** will be discussed. The first photoresist pattern is removed using, for example, ashing and stripping processes. The third insulating layer **216** is deposited on the surface of the
15 resulting structure on which the first and second bit line structures **BL1** and **BL2** are formed. The third insulating layer **216** may include, for example, silicon oxide based material. In some embodiments of the present invention, the first and second bit lines **208a** and **208b** include tungsten. The third insulating layer **216** may be deposited using a
20 high temperature oxide film which is deposited at the high temperature and/or using an oxide film such as BPSG and SOG which are required to perform a high temperature baking process after the deposition process. In embodiments employing tungsten, the tungsten may be oxidized exposing the side portions of the first and second bit lines **208a** and **208b**. Accordingly, in order to reduce the likelihood of exposing the bit lines, *i.e.* reduce the likelihood that the tungsten will oxidize, the third insulating layer **216** may be
25 formed by using high density plasma (HDP) oxide film which can be deposited at a low temperature while burying the gap without creating voids.

The surface of the third insulating layer **216** is planarized by performing the CMP process. The second and fourth patterns **210a** and **210b** of the second insulating layer may be used as a stopper. Alternatively, if the optional anti-reflection layer is formed on
30 the second insulating layer as discussed above, the CMP process can be carried out by using the anti-reflection layer as the stopper. The CMP process can be partially performed with respect to an upper portion of the first and second patterns **210a** and **210b** of the second insulating layer **210**. Furthermore, the insulating layer **210**

including, for example, silicon oxide based material, can be again deposited on the surface of the planarized third insulating layer **216** after performing the CMP process with respect to the first and second patterns **210a** and **210b** of the second insulating layer.

Referring now to **Figures 11A and 11B**, methods of forming the storage node contact hole **218** will be discussed. A second photoresist pattern **217** for defining the contact hole area is formed on the planarized third insulating layer **216** by, for example, performing a photo process. The second photoresist pattern **217** is formed in a line shape which is perpendicular to the first and second bit line structures **BL1** and **BL2**. If the second photoresist pattern **217** has the line shape, the align margin can be increased when the photo process is carried out as compared with a hole type second photoresist pattern. In other words, if the hole type contact pattern is used, the layer surrounding the upper portion and the sidewall of the bit line may be deformed when the misalign occurs, thus causing the uniformity of the self-aligned contact forming process may be deteriorated. In contrast, if the contact pattern is formed in the line shape, the self-aligned contact forming process may be uniformly carried and may not be influenced by the misaligning problem.

The third and first insulating layers **216** and **205** are etched with the high etching selectivity with respect to the first and second patterns **210a** and **210b** of the second insulating layer. The second photoresist pattern **217** is used as the etching mask. Since the sidewall spacer does not exist on the sidewalls of the first and second bit lines **208a** and **208b**, the etching process can be carried out with a high etching selectivity condition. Accordingly, the storage node contact hole **218**, which is self-aligned with respect to the first and second bit line structures **BL1** and **BL2**, is formed. Simultaneously, the first residue **216a** of the third insulating layer having the thickness corresponding to the width difference between the first pattern **210a** of the second insulating layer and the first bit line remains at the sidewall of the first bit line structure **BL1** in the storage node contact hole **218**. Similarly, the second residue **216a** of the third insulating layer having the thickness corresponding to the width difference between the second pattern **210b** of the second insulating layer and the second bit line remains at the sidewall of the second bit line structure **BL2**.

Referring now to **Figures 12A and 12B**, methods of forming first and second sidewall spacers **220a** and **220b** will be discussed. As discussed above, after forming the storage node contact hole **218**, the ashing and stripping processes are carried out so as to

remove the second photoresist pattern **217**. The fourth insulating layer having the thickness of below about 400 Å is formed on the surface of the resulting structure. The fourth insulating layer is anisotropically etched.

Accordingly, the first sidewall spacer **220a** is formed on the sidewall of the first residue **216a** of the third insulating layer and on the sidewall of the first pattern **205a** of the first insulating layer in the storage node contact hole **218**. Similarly, the second sidewall spacer **220b** is formed on the sidewall of the second residue **216b** of the third insulating layer and on the sidewall of the second pattern **205b** of the first insulating layer.

The fourth insulating layer is typically formed by using, for example, silicon oxide based material or silicon nitride based material, or may be a composite layer consisting of silicon oxide based material and silicon nitride based material. For example, oxide material, which is deposited at the low temperature and has a good step coverage on the stepped portion, may be used as the fourth insulating layer.

Alternatively, the fourth insulating layer may be deposited by using a liquid phase deposition (LPD) process. As explained with reference to **Figure 3E**, the fourth insulating layer may be formed by the method disclosed in an article by J.W. Klaus *et al* entitled *Atomic layer deposition of SiO₂ using catalyzed and uncatalyzed self-limiting surface reaction*. Surface Review and Letters, Volume 6, Nos. 3 & 4, pages 435-448 (1999).

Referring now to **Figures 13A and 13B**, methods of forming the capacitor conductive layer **222** will be discussed. The capacitor conductive layer **222** is deposited using a chemical vapor deposition process. The capacitor conductive layer **222** may include, for example, a doped polysilicon layer. The capacitor conductive layer **222** may be removed to partially or substantially expose the upper surface of the third insulating layer **216** in such a manner that the capacitor conductive layer **222** remains substantially in the storage node contact hole **218**. The capacitor conductive layer **222** may be removed by using an etch back method or a CMP process. The capacitor conductive layer **222** can be patterned as a storage electrode pattern using a photolithography process.

A capacitor (not shown) may be formed using processes known to those having skill in the art. The capacitor is electrically connected to the source region **205a** through the storage node contact hole **218** and consists of the storage electrode, a dielectric film

and a plate electrode.

As mentioned above, according to the embodiments of the present invention, the possibility that a bit line will be exposed may be reduced by the addition of the third insulating layer residue on the sidewall of the bit line. Furthermore, the thickness of the sidewall spacer surrounding the sidewall of the bit line may increase by the thickness of the residue, so the number of shorts between the bit line and the contact may also be reduced as well as the current leakage.

Since the sidewall spacer is formed on the sidewall of the bit line structures after forming the storage node contact hole using the self-aligned contact forming process, the sidewall spacer can be made of a silicon oxide based insulating layer having a low dielectric constant. Accordingly, the parasitic capacitance between the bit lines can be reduced, thereby possibly enhancing the operating speed of the device.

Furthermore, the photoresist pattern, *i.e.* contact pattern, used to form the storage node contact hole is formed in a line shape as opposed to a hole shape, thus, the aligning margin may be increased when the photo process is carried out and the process uniformity is improved.

As discussed above, the present invention provides integrated circuit devices providing improved short prevention and methods of fabricating the same. According to embodiments of the present invention, an insulating layer includes an overhanging portion that extends beyond the conductive layer. A sidewall insulating region, *i.e.* insulating layer residue, is disposed laterally in the space between the overhanging portion of the insulating layer and the microelectronic substrate. Accordingly, this sidewall insulating region may reduce the possibility that the conductive layer will be exposed when the contact hole is etched. Furthermore, the thickness of the sidewall spacer formed on the sidewall of the conductive layer increases by the thickness of the sidewall insulating region, thus, the current leakage generated in the conductive layer may be reduced.

In the drawings and specification, there have been disclosed typical preferred embodiments of the invention and, although specific terms are employed, they are used in a generic and descriptive sense only and not for purposes of limitation, the scope of the invention being set forth in the following claims.